## Low Saturation Voltage

## PNP Silicon Driver Transistors

Part of the GreenLine ${ }^{\text {TM }}$ Portfolio of devices with energy-conserving traits.
MMBT1010LT1 MSD1010T1

This PNP Silicon Epitaxial Planar Transistor is designed to conserve energy in general purpose driver applications. This device is housed in the SOT-23 and SC-59 packages which are designed for low power surface mount applications.

- Low $\mathrm{V}_{\mathrm{CE} \text { (sat) }},<0.1 \mathrm{~V}$ at 50 mA


## Applications

- LCD Backlight Driver
- Annunciator Driver
- General Output Device Driver


## MAXIMUM RATINGS ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ )

| Rating | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Collector-Base Voltage | $\mathrm{V}_{(\mathrm{BR}) \mathrm{CBO}}$ | 45 | Vdc |
| Collector-Emitter Voltage | $\mathrm{V}_{\text {(BR)CEO }}$ | 15 | Vdc |
| Emitter-Base Voltage | $\mathrm{V}_{(\mathrm{BR}) \text { EBO }}$ | 5.0 | Vdc |
| Collector Current - Continuous | $\mathrm{I}_{\mathrm{C}}$ | 100 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
| :--- | :---: | :---: | :---: |
| Power Dissipation | $\mathrm{P}_{\mathrm{D}}(1)$ | 250 | mW |
| $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ <br> Derate above $25^{\circ} \mathrm{C}$ |  | 1.8 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Thermal Resistance, Junction to Ambient | $\mathrm{R}_{\text {өJA }}$ | 556 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction Temperature | $\mathrm{T}_{\mathrm{J}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\text {stg }}$ | $-55-+150$ | ${ }^{\circ} \mathrm{C}$ |

## DEVICE MARKING

MMBT1010LT1 = GLP; MSD1010T1 = GLP
LECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Condition | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-Emitter Breakdown Voltage | $\mathrm{V}_{\text {(BR)CEO }}$ | $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=0$ | 15 | - | Vdc |
| Emitter-Base Breakdown Voltage | $\mathrm{V}_{\text {(BR)EBO }}$ | $\mathrm{I}_{\mathrm{E}}=10 \mu \mathrm{~A}, \mathrm{I}_{\mathrm{E}}=0$ | 5.0 | - | Vdc |
| Collector-Base Cutoff Current | $\mathrm{I}_{\text {сво }}$ | $\mathrm{V}_{C B}=20 \mathrm{~V}, \mathrm{I}_{\mathrm{E}}=0$ | - | 0.1 | $\mu \mathrm{A}$ |
| Collector-Emitter Cutoff Current | 1 Ceo | $\mathrm{V}_{\mathrm{CE}}=10 \mathrm{~V}, \mathrm{I}_{\mathrm{B}}=0$ | - | 100 | $\mu \mathrm{A}$ |
| DC Current Gain | $\mathrm{h}_{\text {FE1 }}(2)$ | $\mathrm{V}_{\mathrm{CE}}=5 \mathrm{~V}, \mathrm{I}_{\mathrm{C}}=100 \mathrm{~mA}$ | 300 | 600 | - |
| Collector-Emitter Saturation Voltage | $\mathrm{V}_{\text {CE(sat) }}(2)$ | $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=1.0 \mathrm{~mA}$ | - | 0.1 | Vdc |
|  |  | $\mathrm{I}_{\mathrm{C}}=50 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=5.0 \mathrm{~mA}$ | - | 0.1 |  |
|  |  | $\mathrm{I}_{\mathrm{C}}=100 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=10 \mathrm{~mA}$ |  | 0.19 |  |
| Base-Emitter Saturation Voltage | $\mathrm{V}_{\text {BE(sat) }}(2)$ | $\mathrm{I}_{\mathrm{c}}=100 \mathrm{~mA}, \mathrm{I}_{\mathrm{B}}=10 \mathrm{~mA}$ | - | 1.1 | Vdc |

(1) Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.
(2) Pulse Test: Pulse Width $\leq 300 \mu \mathrm{~s}$, D.C $\leq 2 \%$.

